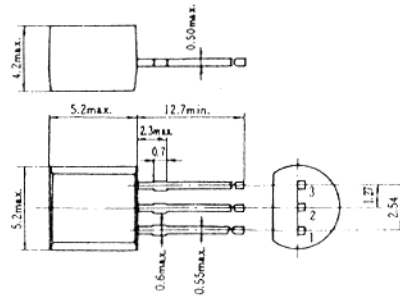


2SA1025, 2SA1081, 2SA1082

SILICON PNP EPITAXIAL

LOW FREQUENCY AMPLIFIER

Complementary pair with 2SC2396, 2SC2543
and 2SC2544



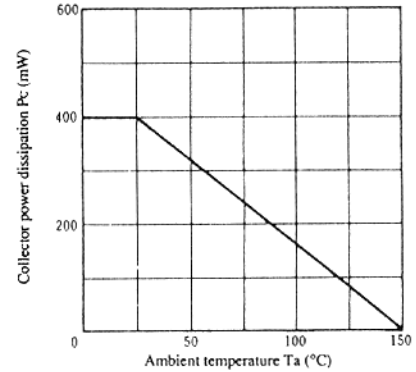
1. Emitter
 2. Collector
 3. Base
- (Dimensions in mm)

(JEDEC TO-92)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1025	2SA1081	2SA1082	Unit
Collector to base voltage	V _{CB0}	-60	-90	-120	V
Collector to emitter voltage	V _{CEO}	-60	-90	-120	V
Emitter to base voltage	V _{EBO}	-5	-5	-5	V
Collector current	I _C	-100	-100	-100	mA
Emitter current	I _E	100	100	100	mA
Collector power dissipation	P _C	400	400	400	mW
Junction temperature	T _j	150	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-55 to +150	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	2SA1025			2SA1081			2SA1082			Unit
			min.	typ.	max.	min.	typ.	max.	min.	typ.	max.	
Collector to base break-down voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-60	—	—	-90	—	—	-120	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-60	—	—	-90	—	—	-120	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-5	—	—	-5	—	—	-5	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -50V, I _E = 0	—	—	-0.1	—	—	-0.1	—	—	-0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -2V, I _C = 0	—	—	-0.1	—	—	-0.1	—	—	-0.1	μA
DC current transfer ratio	h _{FE} *	V _{CE} = -12V, I _C = -2mA	250	—	800	250	—	800	250	—	800	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1mA	—	—	-0.2	—	—	-0.2	—	—	-0.2	V
Base to emitter voltage	V _{BE}	V _{CE} = -12V, I _C = -2mA	—	-0.6	—	—	-0.6	—	—	-0.6	—	V
Gain bandwidth product	f _T	V _{CE} = -12V, I _C = -2mA	—	90	—	—	90	—	—	90	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	3.5	—	—	3.5	—	—	3.5	—	pF

D	E
250 to 500	400 to 800